Vincotech

10-EZ124PA020MS-LQ18F78T
datasheet

fastPACK E1 SiC **1200 V / 20 mΩ**

Topology features

- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Target applications

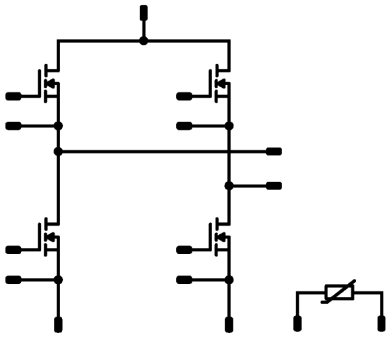
- Charging Stations
- Power Supply
- UPS
- Welding & Cutting

Types

- 10-EZ124PA020MS-LQ18F78T

flow E1 12 mm housing

Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	T_j = T_{jmax} T_s = 80 °C	66	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	240	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	130	W
Gate-source voltage	V_{GSS}	static	-5 / 18	V
		dynamic	-10 / 22	V
Maximum Junction Temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			8,62	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		18		60	25 125 150		22,5 26,2 28,3	29,5[1]	mΩ
Gate-source threshold voltage	$V_{GS(th)}$				0,006	25	1,7	2,25	2,75	V
Gate to Source Leakage Current	I_{GSS}		22	0		25			200	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			20	µA
Internal gate resistance	r_g							1		Ω
Gate charge	Q_g		-5/18	800	80	25		170		nC
Short-circuit input capacitance	C_{iss}	f = 500 kHz	0	800	0	25		4000		pF
Short-circuit output capacitance	C_{oss}							224		
Reverse transfer capacitance	C_{rss}							10		
Diode forward voltage	V_{SD}		0		60	25		4,1		V
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{pastc} = 3,4 W/mK (PSX)						0,73		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	-5/18	600	60	25 125 150		35,81 31,94 31,28		ns
Rise time	t_r					25 125 150		20,15 16,05 15,3		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		65,48 74,84 77,11		ns
Fall time	t_f					25 125 150		16,92 15,35 17,38		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,351 µC Q_{rFWD}=0,94 µC Q_{rFWD}=1,13 µC				25 125 150		1,05 1,18 1,22		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,296 0,319 0,326		mWs
Peak recovery current	I_{RRM}	di/dt=3589 A/µs di/dt=3995 A/µs di/dt=3713 A/µs				25 125 150		25,52 45,71 51,95		A
Reverse recovery time	t_{rr}					25 125 150		33,67 31,28 32,25		ns
Recovered charge	Q_r					25 125 150		0,351 0,94 1,13		µC
Reverse recovered energy	E_{rec}					25 125 150		0,076 0,25 0,316		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		2163,82 3470,31 5788,73		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 493 Ω				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %						3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %						3437		K
Vincotech Thermistor Reference									K	

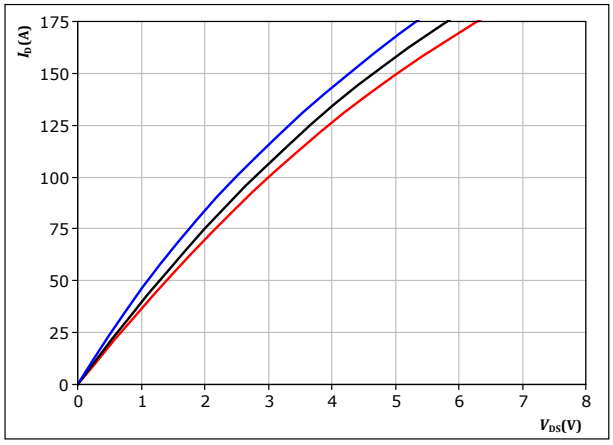
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

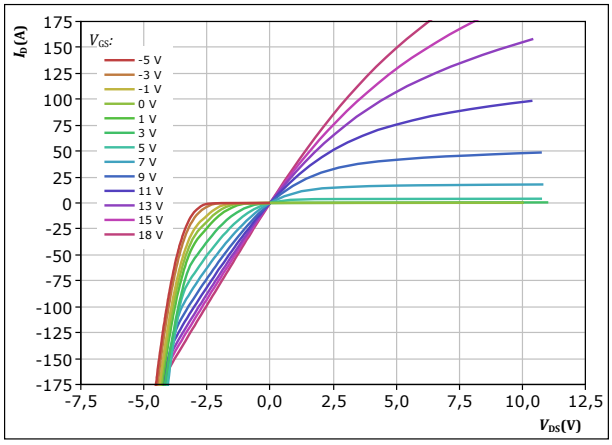


t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$



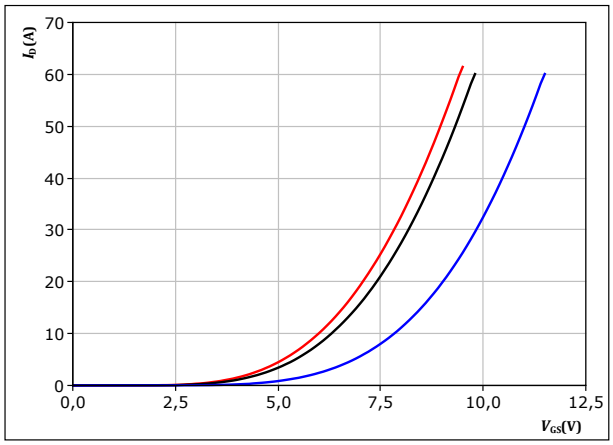
t_p =	250	µs
T_j =	150	°C

V_{GS} from -5 V to 18 V in steps of 2 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

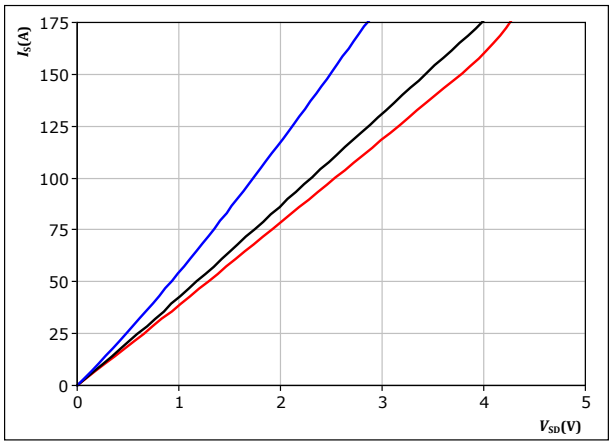


t_p =	250	µs		
V_{DS} =	10	V	T_j:	25 °C
				125 °C
				150 °C

figure 4. **MOSFET**

Typical reverse drain current characteristics

$I_{SD} = f(V_{SD})$



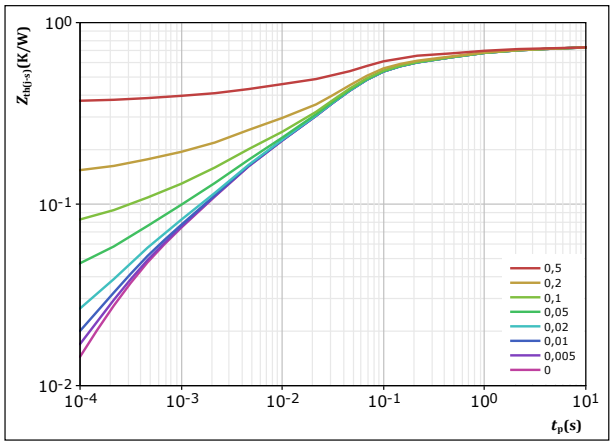
t_p =	250	µs		
V_{GS} =	18	V	T_j:	25 °C
				125 °C
				150 °C

Inverter Switch Characteristics

figure 5. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,73	K/W

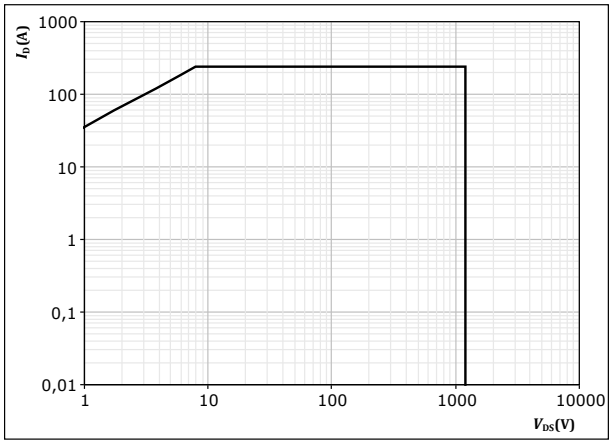
MOSFET thermal model values

R (K/W)	τ (s)
4,84E-02	4,18E+00
1,30E-01	4,60E-01
4,12E-01	4,49E-02
1,06E-01	3,08E-03
3,67E-02	3,11E-04

figure 6. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



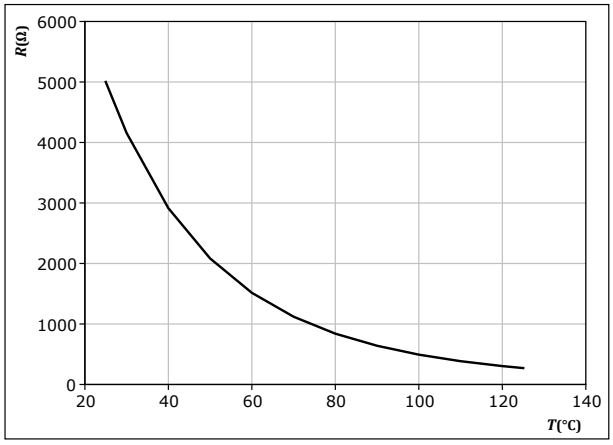
D =	single pulse	
T_s =	80	°C
V_{GS} =	18	V
T_j =	T_{jmax}	

Thermistor Characteristics

figure 7. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

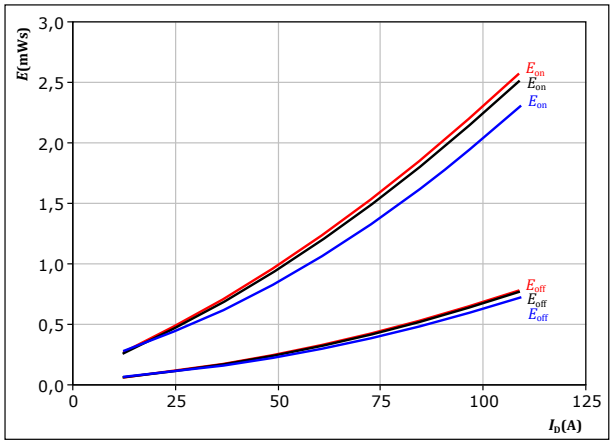


Inverter Switching Characteristics

figure 8. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



With an inductive load at

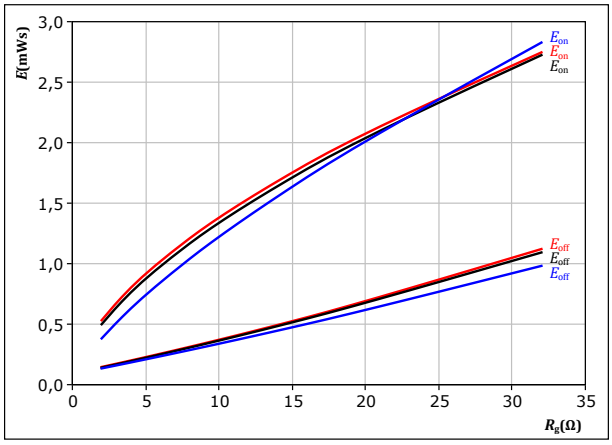
V_{DS} =	600	V
V_{GS} =	-5/18	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 9. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

$E = f(R_g)$



With an inductive load at

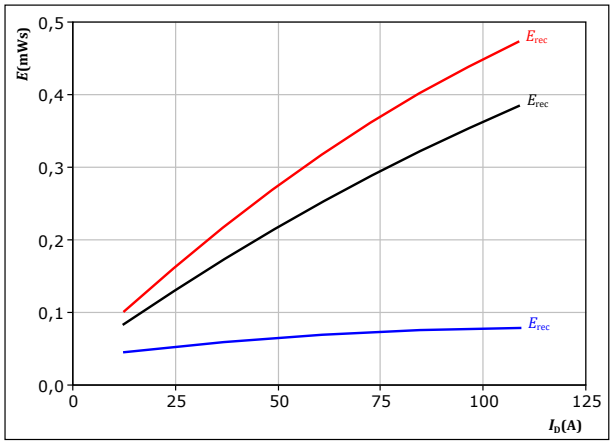
V_{DS} =	600	V
V_{GS} =	-5/18	V
I_D =	60	A

T_j: 25 °C, 125 °C, 150 °C

figure 10. **MOSFET**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



With an inductive load at

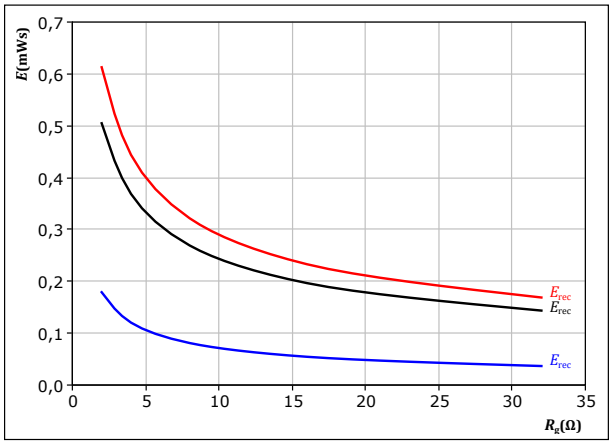
V_{DS} =	600	V
V_{GS} =	-5/18	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 11. **MOSFET**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{DS} =	600	V
V_{GS} =	-5/18	V
I_D =	60	A

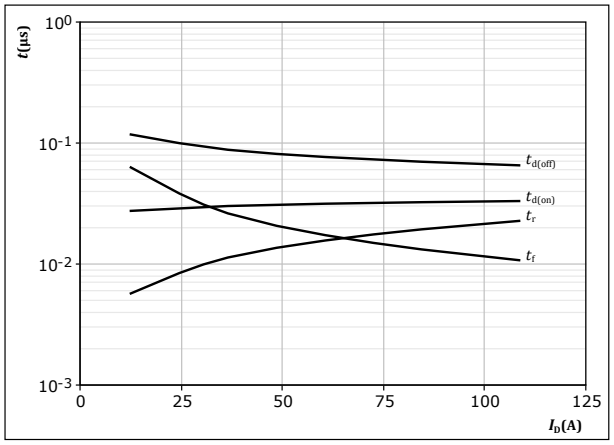
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 12. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



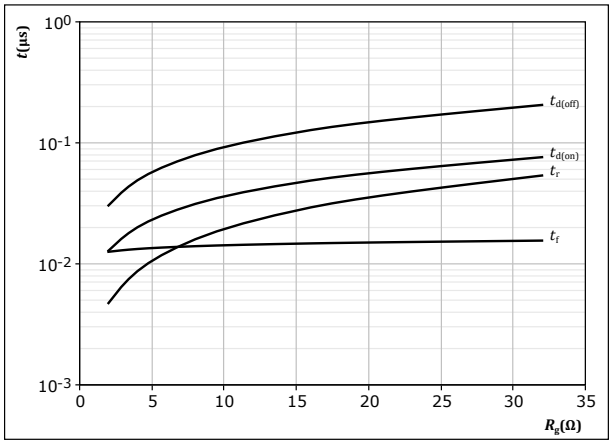
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-5/18	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 13. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

$t = f(R_g)$



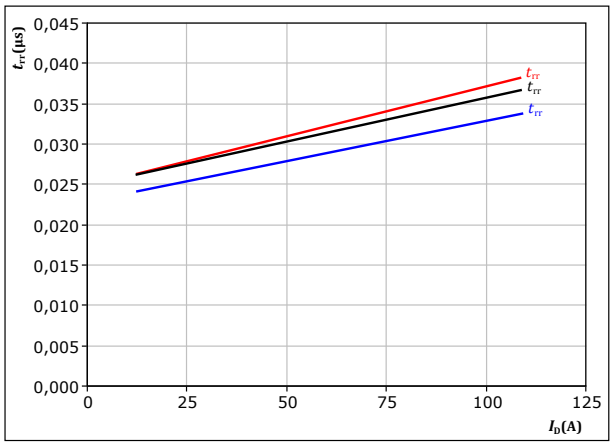
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-5/18	V
I_D =	60	A

figure 14. **MOSFET**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

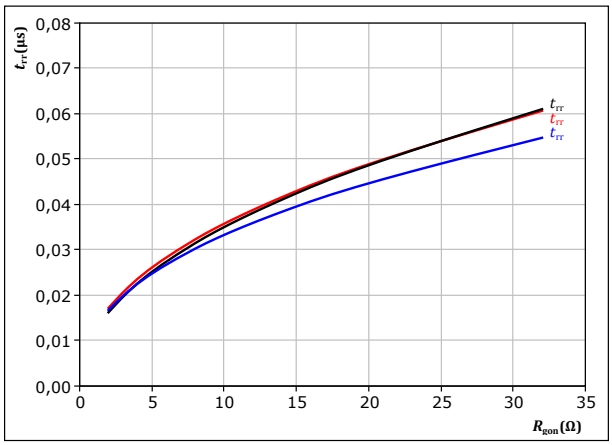
V_{DS} =	600	V
V_{GS} =	-5/18	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 15. **MOSFET**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



At

V_{DS} =	600	V
V_{GS} =	-5/18	V
I_D =	60	A

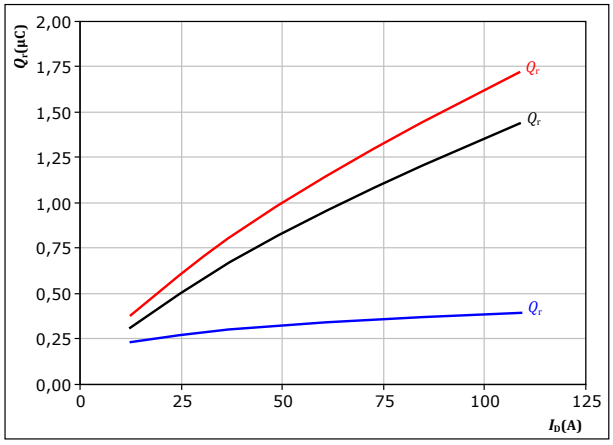
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 16. **MOSFET**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

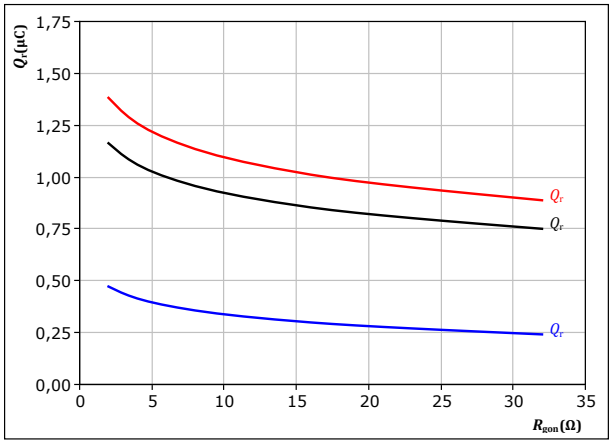


At					
V_{DS} =	600	V	T_j:	25 °C	
V_{GS} =	-5/18	V		125 °C	
R_{gon} =	8	Ω		150 °C	

figure 17. **MOSFET**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

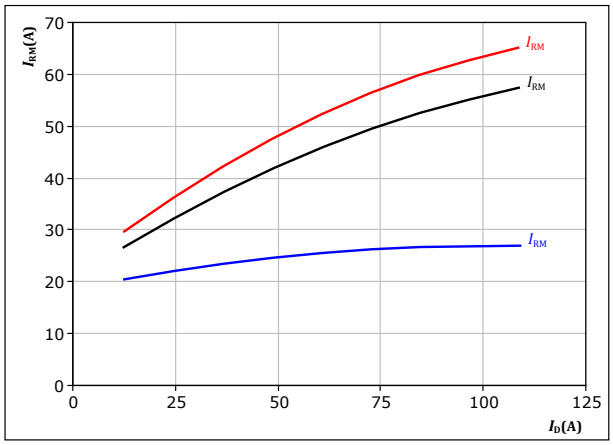


At					
V_{DS} =	600	V	T_j:	25 °C	
V_{GS} =	-5/18	V		125 °C	
I_D =	60	A		150 °C	

figure 18. **MOSFET**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

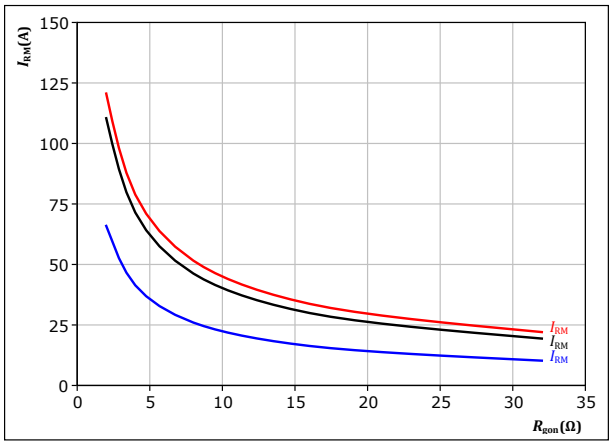


At					
V_{DS} =	600	V	T_j:	25 °C	
V_{GS} =	-5/18	V		125 °C	
R_{gon} =	8	Ω		150 °C	

figure 19. **MOSFET**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



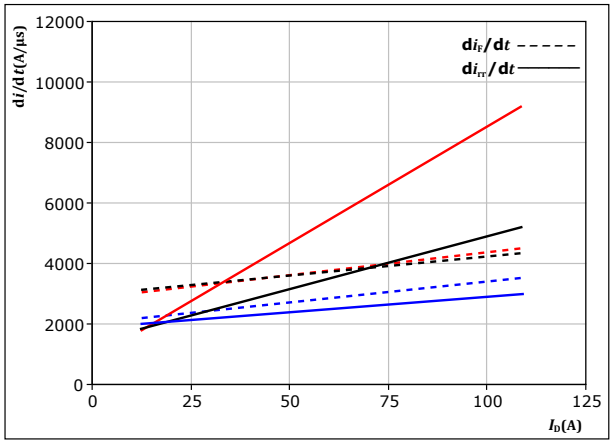
At					
V_{DS} =	600	V	T_j:	25 °C	
V_{GS} =	-5/18	V		125 °C	
I_D =	60	A		150 °C	

Inverter Switching Characteristics

figure 20. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

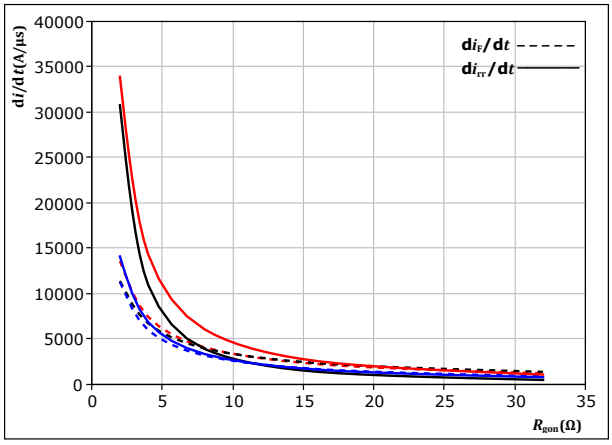


At					
	V_{DS} =	600	V		
	V_{GS} =	-5/18	V	T_j:	25 °C, 125 °C, 150 °C
	R_{gon} =	8	Ω		

figure 21. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

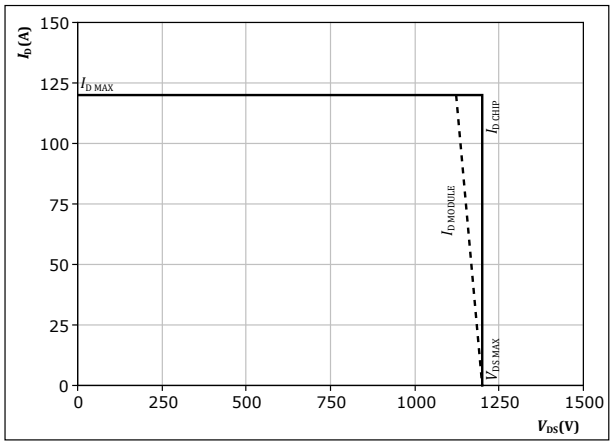


At					
	V_{DS} =	600	V		
	V_{GS} =	-5/18	V	T_j:	25 °C, 125 °C, 150 °C
	I_D =	60	A		

figure 22. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
	T_j =	150	°C
	R_{gon} =	8	Ω
	R_{goff} =	8	Ω

Inverter Switching Definitions

figure 23. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

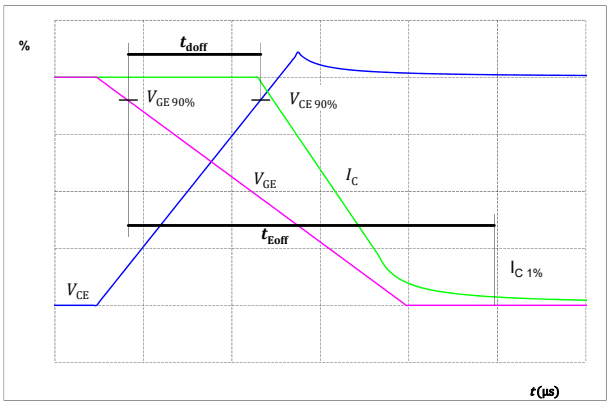


figure 24. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

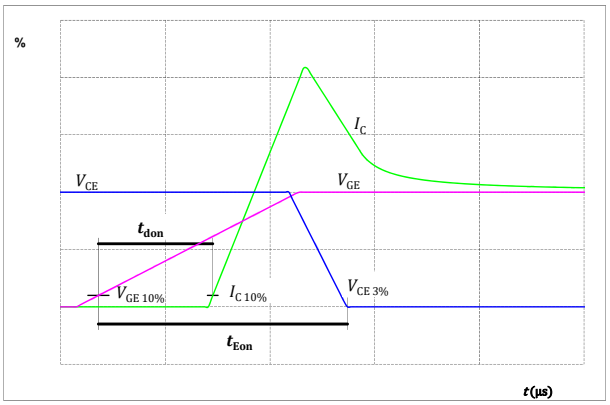


figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_f

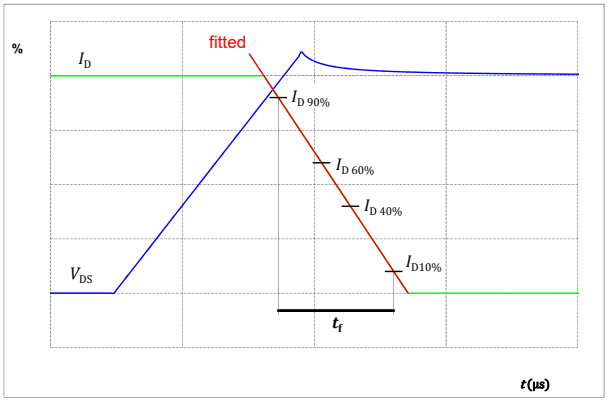
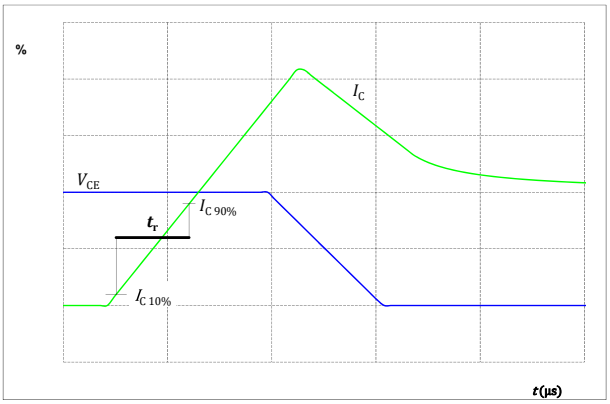


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 27. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

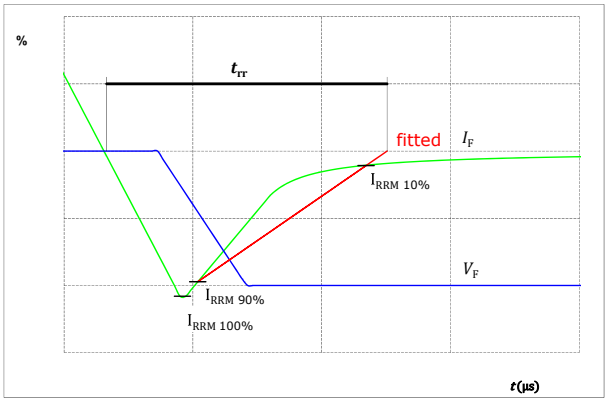


figure 28. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

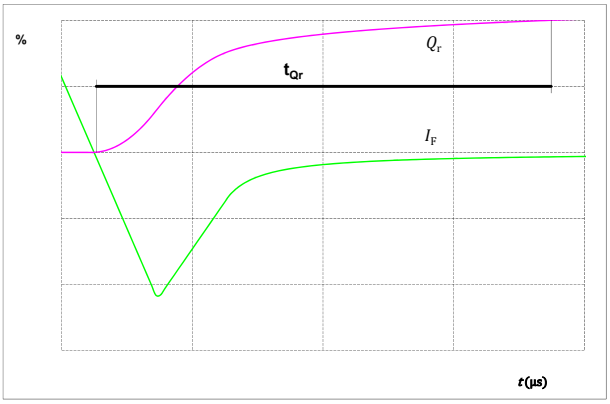
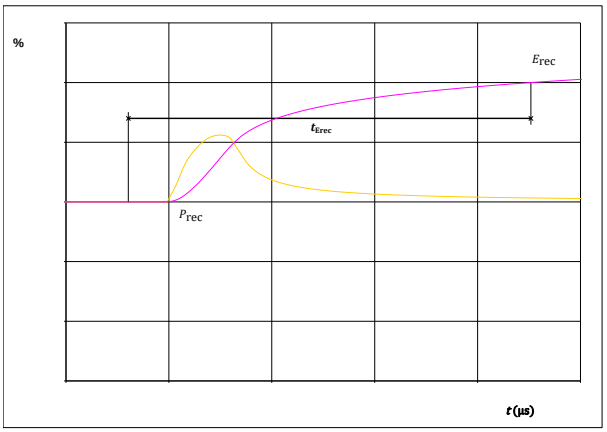


figure 29. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code	
Version	**Ordering Code**
Without thermal paste	10-EZ124PA020MS-LQ18F78T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EZ124PA020MS-LQ18F78T-/7/

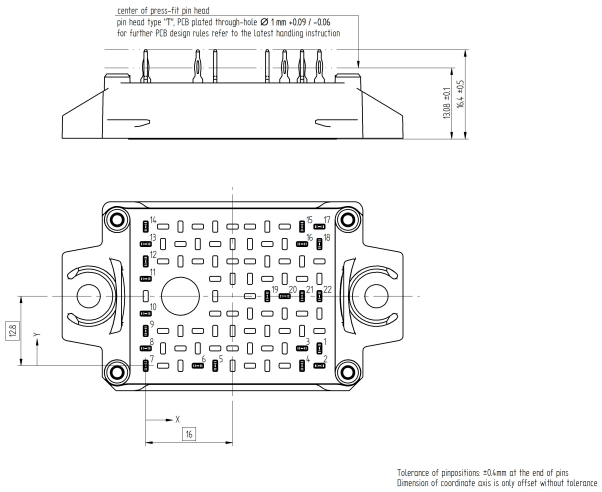
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTVV	LLLLL	SSSS	WWYY		

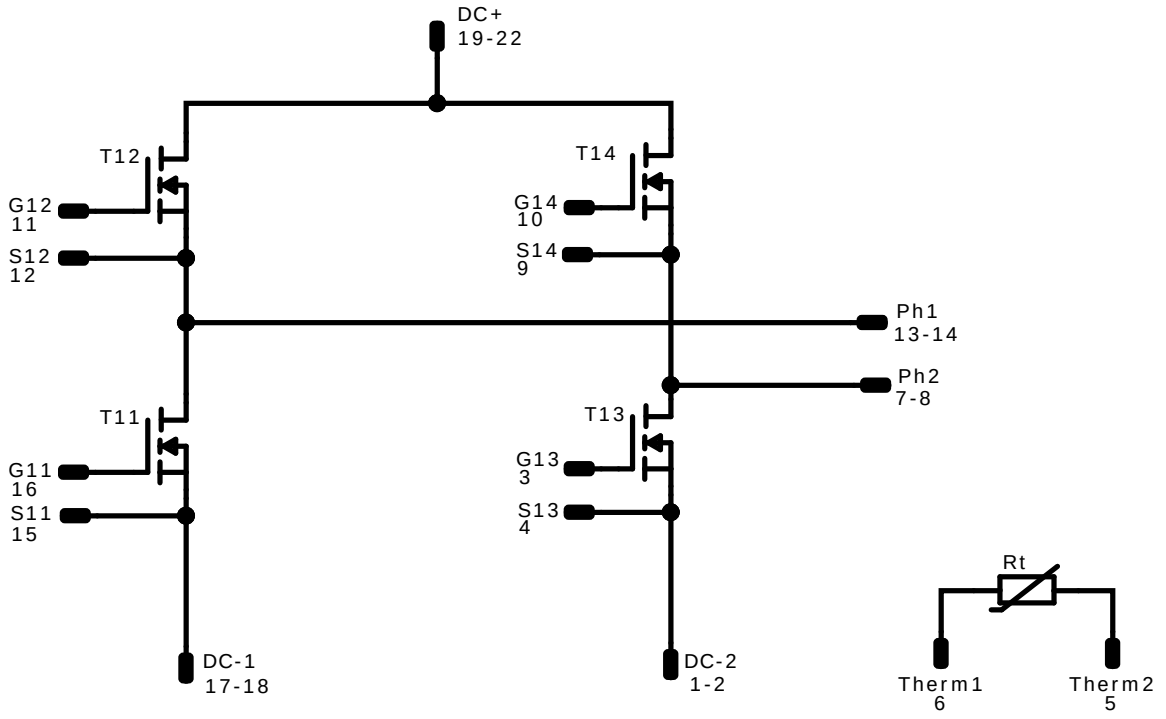
Outline

Pin table [mm]

Pin	X	Y	Function
1	32	3,2	DC-2
2	32	0	DC-2
3	28,8	3,2	G4
4	28,8	0	S4
5	12,8	0	T2
6	9,6	0	T1
7	0	0	AC2
8	0	3,2	AC2
9	0	6,4	S3
10	0	9,6	G3
11	0	16	G1
12	0	19,2	S1
13	0	22,4	AC1
14	0	25,6	AC1
15	28,8	25,6	S2
16	28,8	22,4	G2
17	32	25,6	DC-1
18	32	22,4	DC-1
19	22,4	12,8	DC+
20	25,6	12,8	DC+
21	28,8	12,8	DC+
22	32	12,8	DC+



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14	MOSFET	1200 V	20 mΩ	Inverter Switch	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-EZ124PA020MS-LQ18F78T-D1-14	6 Aug. 2025	Initial Release	